

Description

The SX68N03NF uses advanced technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 30V$ $I_D = 68A$

$R_{DS(ON)} < 6.0m\Omega$ @ $V_{GS}=10V$

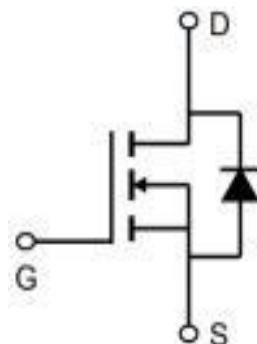
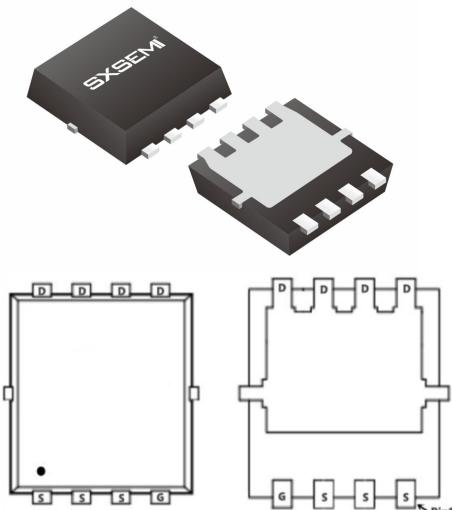
$C_{ISS} \approx 814PF$

Application

Buck And Boost

Wireless impact

Car charging

PDFN5*6-8L**Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)**

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_c=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	68	A
$I_D @ T_c=75^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	35	A
I_{DM}	Pulsed Drain Current ²	150	A
EAS	Single Pulse Avalanche Energy ³	28.8	mJ
I_{AS}	Avalanche Current	24	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation ⁴	24	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	25	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	5.2	$^\circ C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$	30	---	---	V
RDS(ON)	Static Drain-Source On-Resistance ²	$V_{GS}=10\text{V}$, $I_D=20\text{A}$	---	4.8	6.0	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=15\text{A}$	---	6.9	9.0	
VGS(th)	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu\text{A}$	1.2	1.6	2.5	V
IDSS	Drain-Source Leakage Current	$V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	1	uA
		$V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$, $T_J=55^\circ\text{C}$	---	---	5	
IGSS	Gate-Source Leakage Current	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$	---	---	± 100	nA
gfs	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=30\text{A}$	---	43	---	S
R _g	Gate Resistance	$V_{DS}=0\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	---	1.7	---	Ω
Q _g	Total Gate Charge (4.5V)	$V_{DS}=15\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=15\text{A}$	---	8	---	nC
Qgs	Gate-Source Charge		---	2.4	---	
Qgd	Gate-Drain Charge		---	3.2	---	
Td(on)	Turn-On Delay Time	$V_{DD}=15\text{V}$, $V_{GS}=10\text{V}$, $R_G=3.3\Omega$, $I_D=15\text{A}$	---	7.1	---	ns
T _r	Rise Time		---	40	---	
Td(off)	Turn-Off Delay Time		---	15	---	
T _f	Fall Time		---	6	---	
Ciss	Input Capacitance	$V_{DS}=15\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	---	814	---	pF
Coss	Output Capacitance		---	498	---	
Crss	Reverse Transfer Capacitance		---	41	---	
I _s	Continuous Source Current ^{1,6}	$V_G=V_D=0\text{V}$, Force Current	---	---	24	A
V _{SD}	Diode Forward Voltage ²	$V_{GS}=0\text{V}$, $I_S=1\text{A}$, $T_J=25^\circ\text{C}$	---	---	1	V
t _{rr}	Reverse Recovery Time	$I_F=15\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$, $T_J=25^\circ\text{C}$	---	34	---	nS
			---	15	---	nC
Q _{rr}	Reverse Recovery Charge					

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3、The EAS data shows Max. rating . The test condition is $V_{DD}=25\text{V}$, $V_{GS}=10\text{V}$, $L=0.1\text{mH}$, $I_{AS}=24\text{A}$
- 4、The power dissipation is limited by 175°C junction temperature
- 5、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

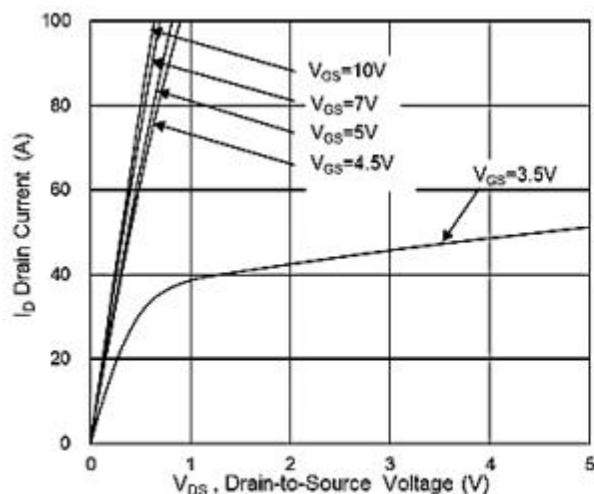


Fig.1 Typical Output Characteristics

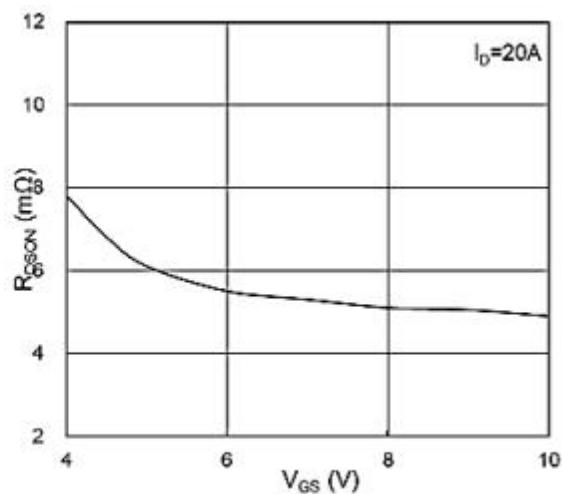


Fig.2 On-Resistance vs G-S Voltage

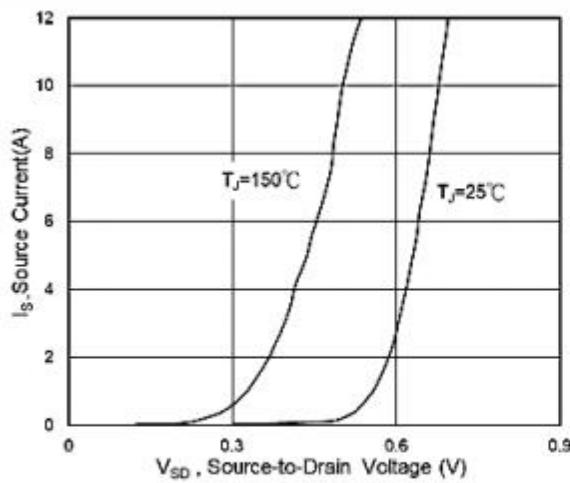


Fig.3 Source Drain Forward Characteristics

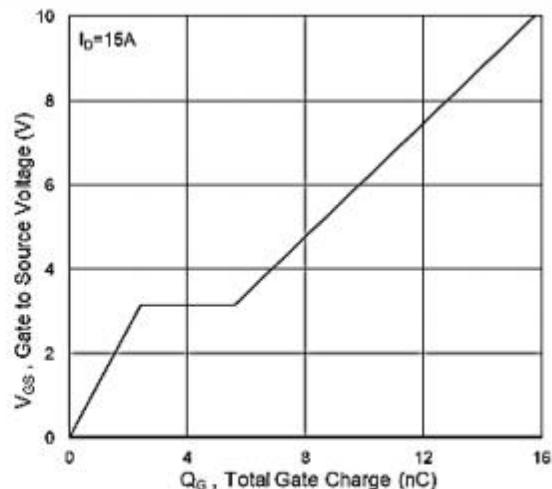


Fig.4 Gate-Charge Characteristics

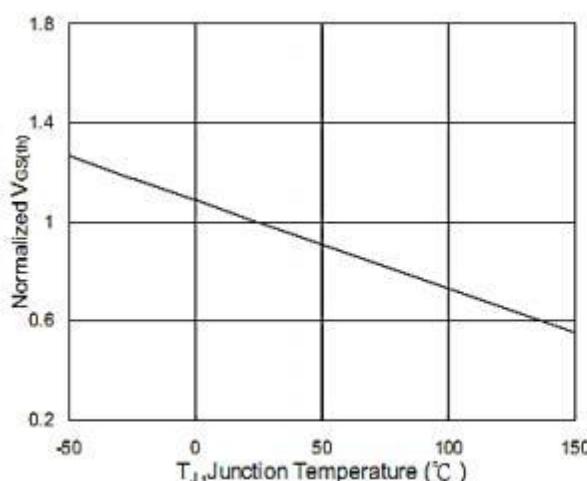


Fig.5 Normalized $V_{GS(th)}$ vs T_J

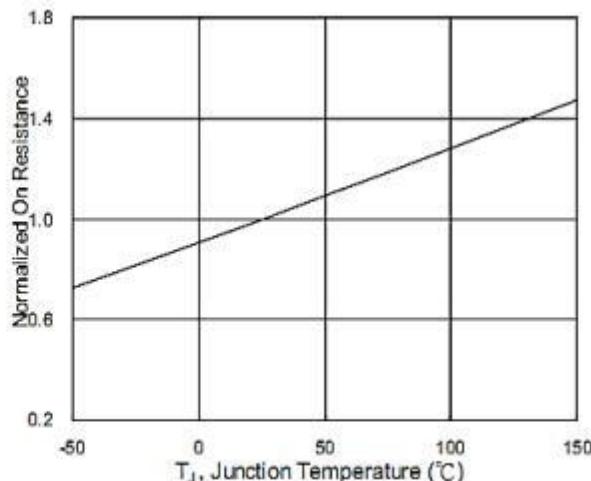


Fig.6 Normalized $R_{DS(on)}$ vs T_J

Typical Characteristics

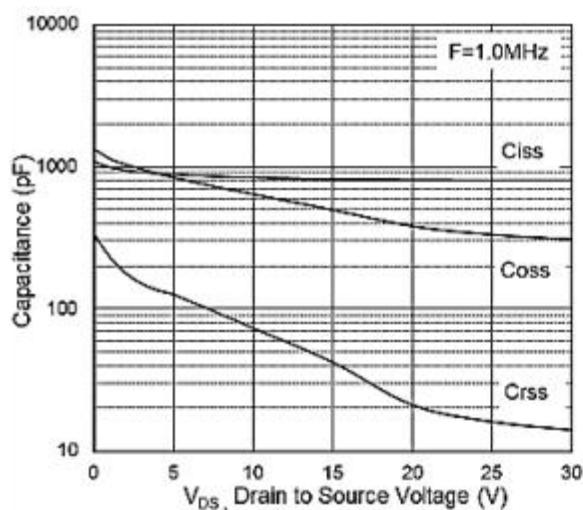


Fig.7 Capacitance

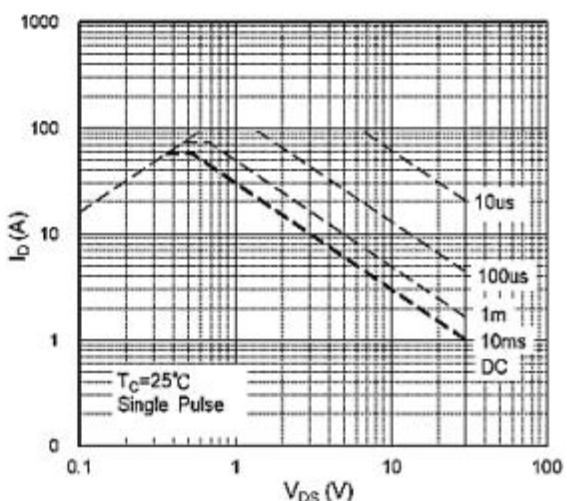


Fig.8 Safe Operating Area

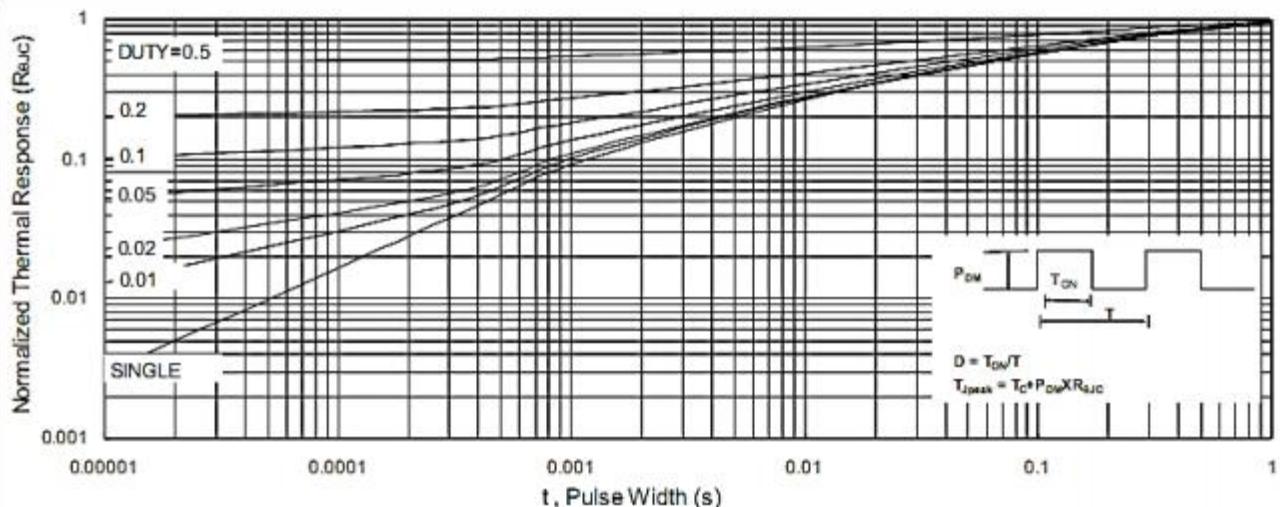


Fig.9 Normalized Maximum Transient Thermal Impedance

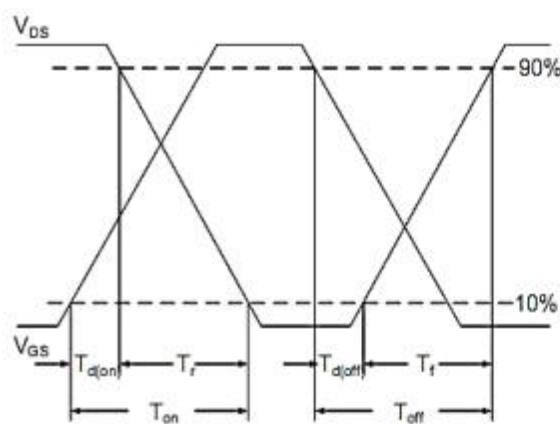


Fig.10 Switching Time Waveform

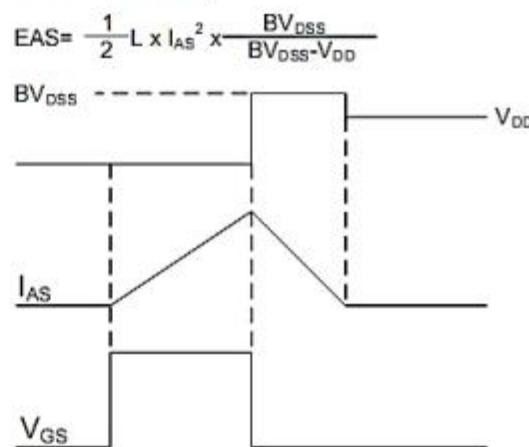
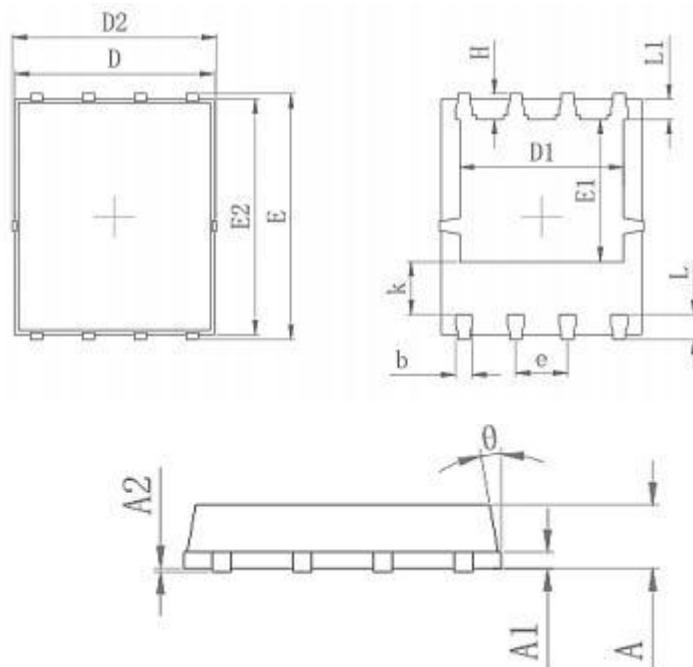


Fig.11 Unclamped Inductive Switching Waveform

Package Mechanical Data-PDFN5*6-8L-XZT Single



Symbol	Common mm	
	Mim	Max
A	0.900	1.100
A1	0.254	
A2	0-0.05	
D	4.824	4.976
D1	3.910	4.110
D2	4.944	5.076
E	5.924	6.076
E1	3.375	3.575
E2	5.674	5.826
b	0.350	0.450
e	1.270	
L	0.534	0.686
L1	0.424	0.576
K	1.190	1.390
H	0.549	0.701
	8 °	12 °

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	PDFN5*6-8L		5000